

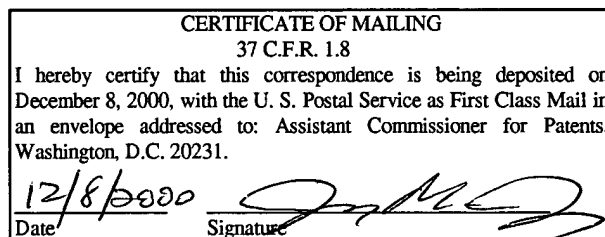
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Xu, et al. §
§
Serial No.: 09/352,008 §
Filed: July 12, 1999 §
For: NEW METHODOLOGIES TO RE- §
DUCE PROCESS SENSITIVITY §
TO THE CHAMBER CONDITION §

Group Art Unit: 1763
Examiner: Bell, B.

#4A
12/19/00
ANW

Assistant Commissioner for Patents
Washington, D.C. 20231



Dear Sir:

RESPONSE TO RESTRICTION REQUIREMENT DATED NOVEMBER 8, 2000

In response to the Restriction Requirement dated November 8, 2000, having a shortened statutory period for response set to expire on December 8, 2000, please enter the following amendments and reconsider the claims pending in the application for reasons discussed below.

IN THE CLAIMS:

Please cancel claims 14-17 without prejudice.

Please amend the following claims:

(Amended) An apparatus for etching a substrate, comprising:

- (a) a process chamber including a chamber body having an internal surface, ;
- (b) one or more sources of one or more etchants coupled to the process chamber; and
- (c) at least one [coil] plasma generator disposed adjacent the process chamber for striking a plasma in the process chamber by disassociating the one or more etchants, wherein a first reaction rate of the disassociated one or more etchants with the internal surface is substantially the same as a second reaction rate of the disassociated one or more etchants with a material formed on the internal surface during processing.

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